

SuperMOS – SOT-23 100V BV_{DSS} , 90m Ω $R_{DS(ON)}$, N-channel MOSFET

1. Description

The NCE0102-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product NCE0102-ES is Pb-free.

2. Features

- 100V, $R_{DS(ON)}$ =90m Ω (TYP.) @ V_{GS} =10V
- $R_{DS(ON)}$ =120m Ω (TYP.) @ V_{GS} =4.5V
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

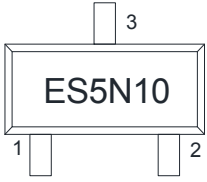
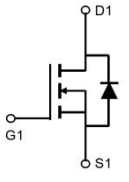
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
NCE0102-ES	SOT-23	ES5N10-ES	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	2.6
		$T_A=75^\circ\text{C}$	2
Maximum Power Dissipation	P_D	1.4	W
Pulsed Drain Current ^A	I_{DM}	10.4	A
Operating Junction Temperature	T_J	150	°C
Lead Temperature	T_L	260	°C
Storage Temperature Range	T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^B	$R_{\theta JA}$		90	°C/W

Note:

A. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 0.85inch x 0.062 inch.

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.65	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.5A$		90	135	m Ω
		$V_{GS}=4.5V, I_D=2A$		120	195	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=25V$		206		pF
Output Capacitance	C_{OSS}			29		
Reverse Transfer Capacitance	C_{RSS}			1.4		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=25V, I_D=2.5A$		4.2		nC
Gate-to-Source Charge	Q_{GS}			1.5		
Gate-to-Drain Charge	Q_{GD}			1.1		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DS}=25V, I_D=2.5A, R_G=2\Omega$		14.7		ns
Rise Time	t_r			3.5		
Turn-Off Delay Time	$t_{d(OFF)}$			20.9		
Fall Time	t_f			2.7		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.0A$		0.8	1.5	V

7. Typical Characteristic

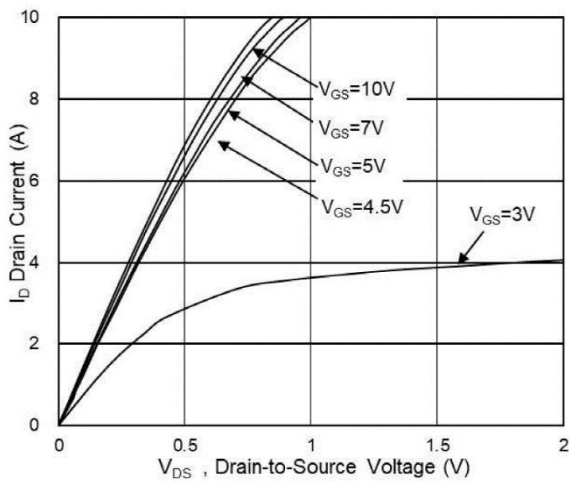


Fig.1 Typical Output Characteristics

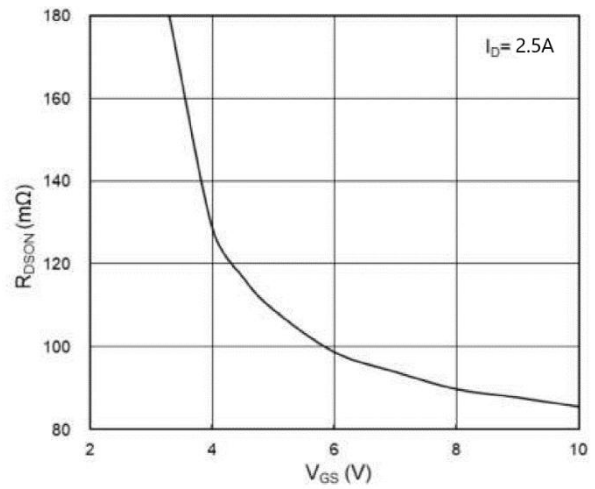


Fig.2 On-Resistance vs G-S Voltage

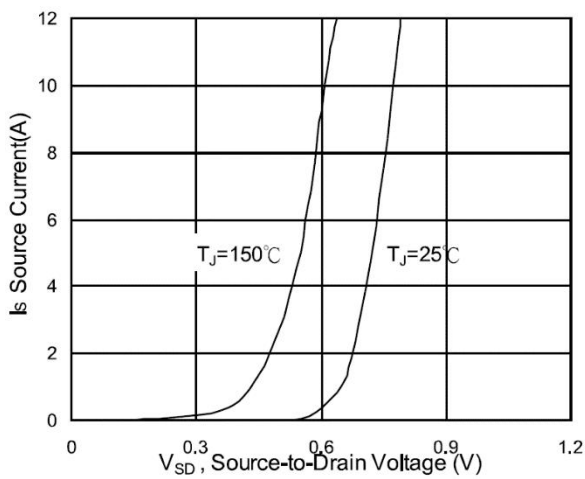


Fig.3 Source Drain Forward Characteristics

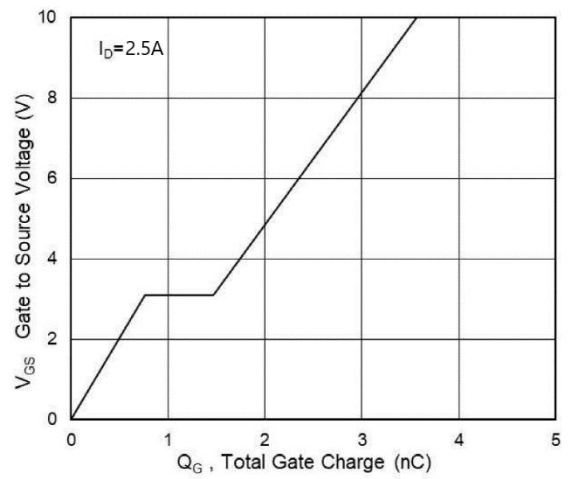


Fig.4 Gate-Charge Characteristics

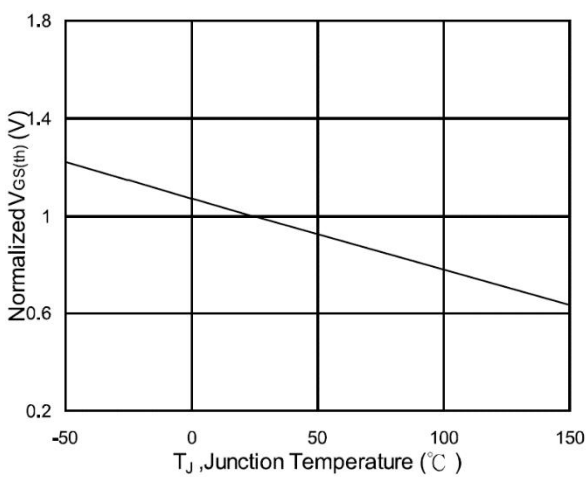


Fig.5 Normalized $V_{GS(th)}$ vs T_J

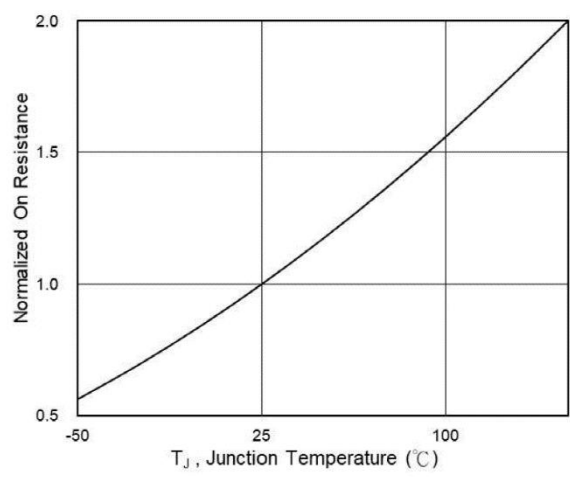
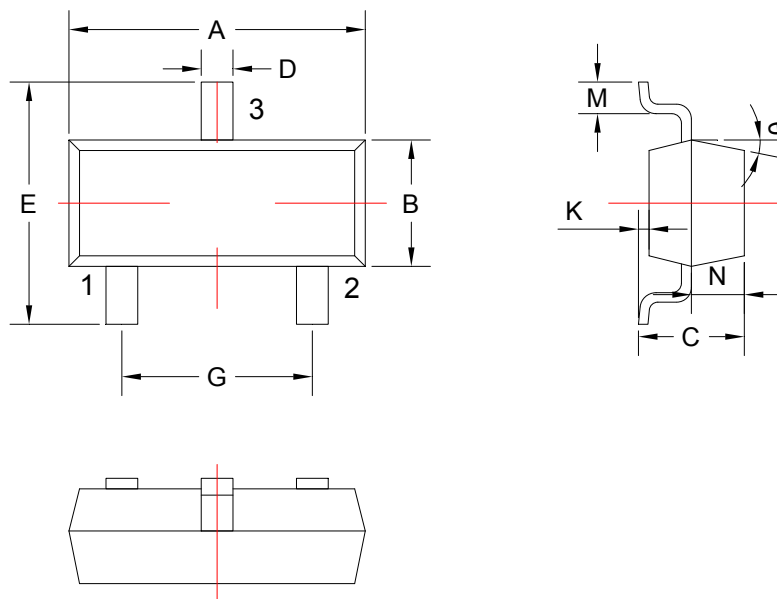


Fig.6 Normalized $R_{DS(on)}$ vs T_J

8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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